

Title (en)

INSULATING STRUCTURES OF BURIED LAYERS WITH BURIED TRENCHES AND METHOD FOR MAKING SAME

Title (de)

ISOLIERENDE STRUKTUREN VERGRABENER SCHICHTEN MIT VERGRABENEN GRÄBEN UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)

STRUCTURE D ISOLATION DE COUCHES ENTERREES PAR TRANCHEES ENTERREES, ET PROCEDE DE FABRICATION

Publication

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Application

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Abstract (en)

[origin: WO02056363A1] The invention concerns an integrated circuit semiconductor substrate comprising at least a dielectrically vertical buried trench and having a height at least five times more than its width, and an epitaxial semiconductor layer (6) covering said trench laterally separating two regions (4, 5). The invention is applicable to MOS, CMOS and BICMOS technologies. The invention also concerns a method for making said substrate.

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IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

See references of WO 02056363A1

Citation (examination)

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